

OPA6316EU

Eutectic Metal

Orange LED Chip

GaAsP / GaP

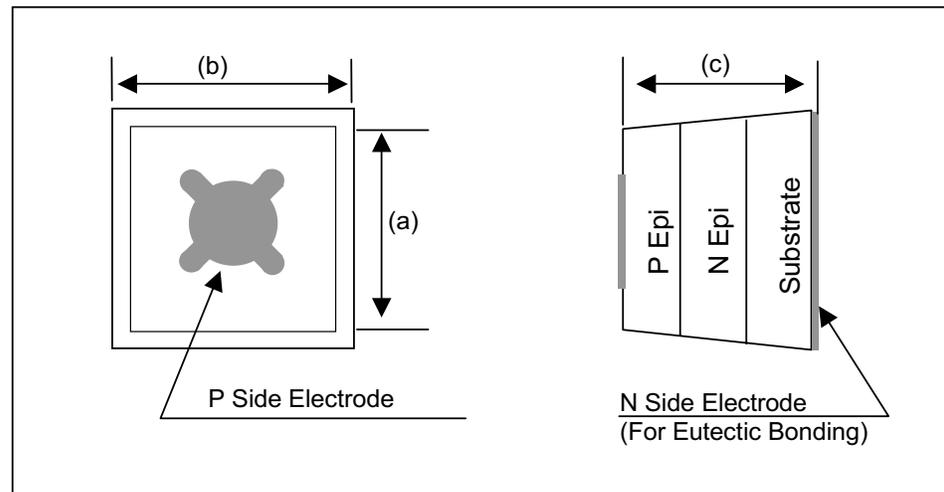
- 1. Material** Substrate GaP (N Type)
Epitaxial Layer GaAsP (P/N Type)
- 2. Electrode** N (Cathode) Side Gold Alloy (AuGe Eutectic Metal)
P (Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	$I_F=1\text{mA}$
	$V_{F(2)}$		1.9	2.2	V	$I_F=20\text{mA}$
Reverse Voltage	V_R	6.0			V	$I_R=10\mu\text{A}$
Brightness	I_V	80	160		mcd	$I_F=20\text{mA}$
Wavelength	Hue		630		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		40		nm	$I_F=20\text{mA}$

※ Note: Assembled into T1^{3/4} plastic package.

- 4. Mechanical Data**
- (a) Emission Area ----- 9mil × 9mil
 - (b) Bottom Area ----- 11mil × 11mil
 - (c) Chip Thickness ----- 11mil



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